

Silicon PNP Power Transistors

2SB755

DESCRIPTION

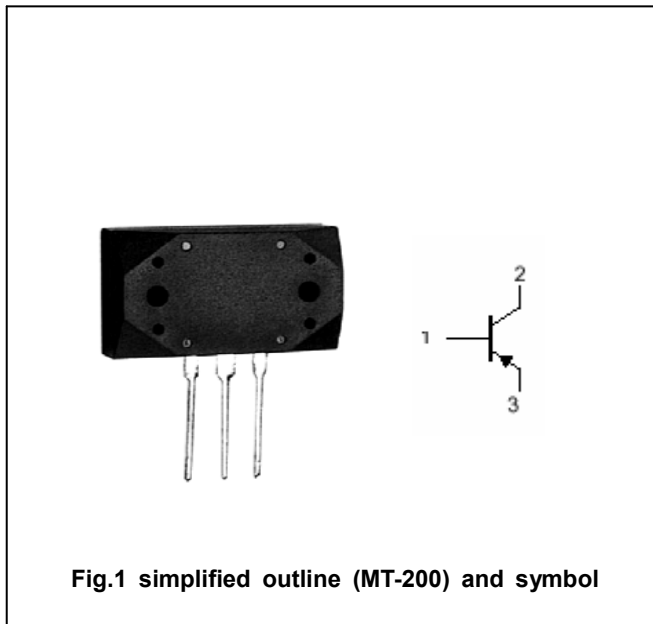
- With MT-200 package
- Complement to type 2SD845
- High transition frequency
- High breakdown voltage : $V_{CEO}=-150V(\text{min})$

APPLICATIONS

- For power amplifier applications

PINNING(see Fig.2)

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter



Absolute maximum ratings (Ta=25°C)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	-150	V
V_{CEO}	Collector-emitter voltage	Open base	-150	V
V_{EBO}	Emitter-base voltage	Open collector	-5	V
I_C	Collector current		-12	A
I_B	Base current		-1.2	A
P_C	Collector power dissipation	$T_C=25^\circ\text{C}$	120	W
T_j	Junction temperature		150	°C
T_{stg}	Storage temperature		-55~150	°C

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CHARACTERISTICS

T_j=25 °C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =-0.1A; I _B =0	-150			V
V _{(BR)EBO}	Emitter-base breakdown voltage	I _E =-10mA; I _C =0	-5			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =-5 A; I _B =-0.5 A			-2.0	V
V _{BE}	Base-emitter on voltage	I _C =-5A ; V _{CE} =-5V			-1.5	V
I _{CBO}	Collector cut-off current	V _{CB} =-150V; I _E =0			-50	μA
I _{EBO}	Emitter cut-off current	V _{EB} =-5V; I _C =0			-50	μA
h _{FE}	DC current gain	I _C =-1A ; V _{CE} =-5V	55		160	
f _T	Transition frequency	I _C =-1A ; V _{CE} =-10V		20		MHz
C _{OB}	Output capacitance	I _E =0; V _{CB} =-10V; f=1MHz		450		pF

◆ h_{FE} classifications

R	O
55-110	80-160

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PACKAGE OUTLINE

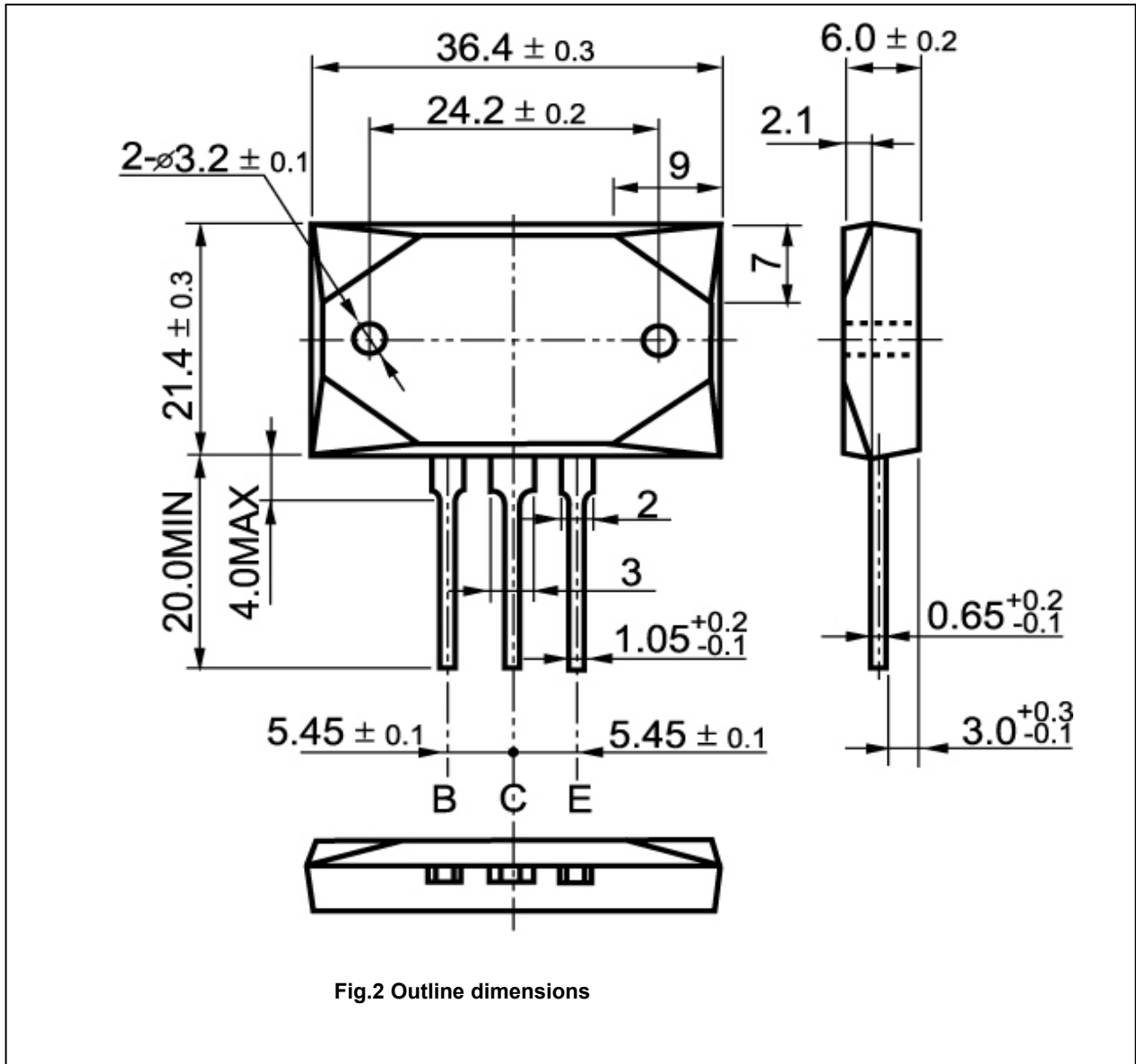


Fig.2 Outline dimensions